



ZVN4306GV

#### SOT223 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

### **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(on)</sub>           | I <sub>D</sub><br>T <sub>A</sub> = +25°C |
|-------------------|-------------------------------|--|
| 60V               | 0.33Ω @ V <sub>GS</sub> = 10V | 2.1A                                     |

### **Features and Benefits**

- BVpss=60V
- RDS(on) =  $0.33\Omega$
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC converters
- · Solenoids/relay driver for automotive applications
- Stepper motor drivers

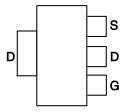
#### **Mechanical Data**

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

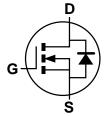




Top View



Pin Out - Top View



Equivalent Circuit

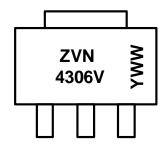
#### **Ordering Information** (Note 4)

| Part Number | Package          | Packing |             |  |
|-------------|------------------|---------|-------------|--|
| Fait Number | Fackage          | Qty.    | Carrier     |  |
| ZVN4306GVTA | SOT223 (Type DN) | 1,000   | Tape & Reel |  |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



 $\begin{tabular}{ll} ZVN4306V &= Product Type Marking Code \\ YWW &= Date Code Marking \\ Y or \overline{Y} &= Last Digit of Year (ex: 1= 2021) \\ WW or \overline{W}W &= Week Code (01~53) \\ \end{tabular}$ 



## Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise stated.)

| Characteristic                          | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Drain-Source Voltage                    | $V_{DS}$                          | 60          | V    |
| Gate-Source Voltage                     | $V_{GS}$                          | ±20         | V    |
| Continuous Drain Current                | I <sub>D</sub>                    | 2.1         | А    |
| Pulsed Drain Current                    | I <sub>DM</sub>                   | 15          | А    |
| Power Dissipation                       | P <sub>tot</sub>                  | 3           | W    |
| Avalanche Current-Repetitive            | IAR                               | 1           | Α    |
| Avalanche Energy-Repetitive             | Ear                               | 25          | mJ   |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise stated.)

| Characteristic                                   | Symbol              | Min | Тур  | Max       | Unit     | Test Condition   |  |
|--|---------------------|-----|------|-----------|----------|--|--|
| OFF CHARACTERISTICS                              |                     |     |      |           |          |  |  |
| Drain-Source Breakdown Voltage                   | BV <sub>DSS</sub>   | 60  | -    | ı         | V        | $V_{GS} = 0V$ , $I_D = 1mA$  |  |
| Zero Gate Voltage Drain Current                  | I <sub>DSS</sub>    | -   | -    | 10<br>100 | μA<br>μA | $V_{DS} = 60V$ , $V_{GS} = 0V$<br>$V_{DS} = 48V$ , $V_{GS} = 0V$ , $T = +125$ °C<br>(Note 6) |  |
| Gate-Body Leakage                                | I <sub>GSS</sub>    | -   | -    | 20        | nA       | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$   |  |
| On-State Drain Current (Note 5)                  | I <sub>D(on)</sub>  | 12  | -    | -         | Α        | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V   |  |
| ON CHARACTERISTICS                               |                     |     |      |           |          |  |  |
| Gate-Source Threshold Voltage                    | $V_{GS(th)}$        | 1.3 | -    | 3         | V        | $V_{DS} = V_{GS}$ , $I_D = 1mA$  |  |
| Statia Drain Source On State Registeres (Note 5) | R <sub>DS(on)</sub> | -   | 0.22 | 0.33      | Ω        | V <sub>GS</sub> = 10V, I <sub>D</sub> =3A  |  |
| Static Drain-Source On-State Resistance (Note 5) |                     | ı   | 0.32 | 0.45      | Ω        | $V_{GS} = 5V, I_D = 1.5A$  |  |
| Forward Transconductance (Notes 5, 6)            | <b>g</b> fs         | 0.7 | -    | ı         | S        | $V_{DS} = 25V, I_D = 3A$   |  |
| DYNAMIC CHARACTERISTICS                          |                     |     |      |           |          |  |  |
| Input Capacitance (Note 6)                       | C <sub>iss</sub>    | ı   | -    | 350       | pF       |  |  |
| Common Source Output Capacitance (Note 6)        | Coss                | ı   | -    | 140       | pF       | $V_{DS} = 25V, V_{GS} = 0V,$   |  |
| Reverse Transfer Capacitance (Note 6)            | C <sub>rss</sub>    | ı   | -    | 30        | pF       | f = 1.0MHz   |  |
| Turn-On Delay Time (Notes 6, 7)                  | t <sub>D(on)</sub>  | ı   | -    | 8         | ns       | VDD ≈25V, VGEN=10V, ID=3A  |  |
| Rise Time (Notes 6, 7)                           | t <sub>R</sub>      | ı   | -    | 25        | ns       |  |  |
| Turn-Off Delay Time (Notes 6, 7)                 | t <sub>D(off)</sub> | ı   | -    | 30        | ns       |  |  |
| Fall Time (Notes 6, 7)                           | t <sub>F</sub>      | -   | -    | 16        | ns       |  |  |

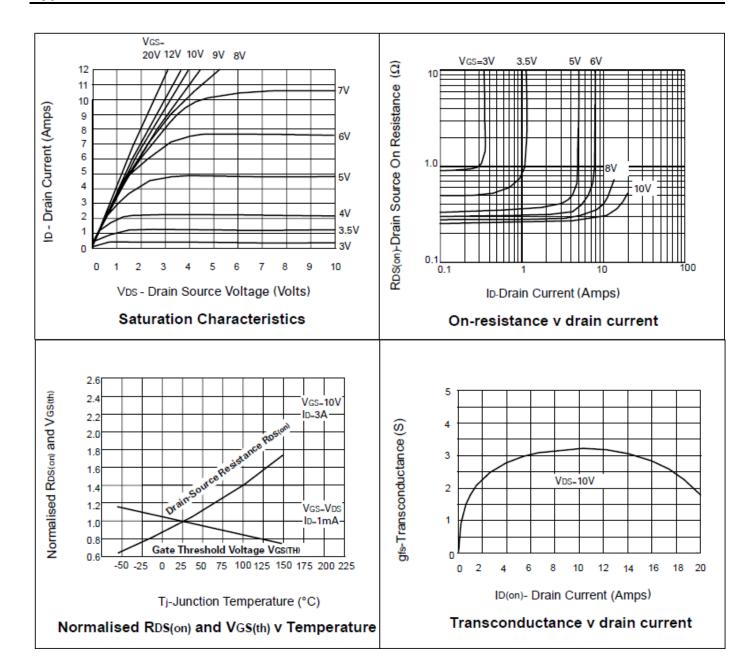
## **Drain-Source Diode Characteristics**

| Characteristic                 | Symbol | Min | Тур  | Max | Unit | Test Condition           |
|--------------------------------|--------|-----|------|-----|------|--------------------------|
| Diode Forward Voltage (Note 5) | Vsp    | -   | 0.82 | -   | V    | Is=0.32A, Vgs=0          |
| Reverse Recovery Time          | Trr    | -   | 112  | -   | ns   | IF=0.32A, Vgs=0, IR=0.1A |

- 5. Measured under pulsed conditions. Width=300 $\mu$ s. Duty cycle  $\leq$ 2%
- 5. Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator. Spice parameter data is available upon request for this device.

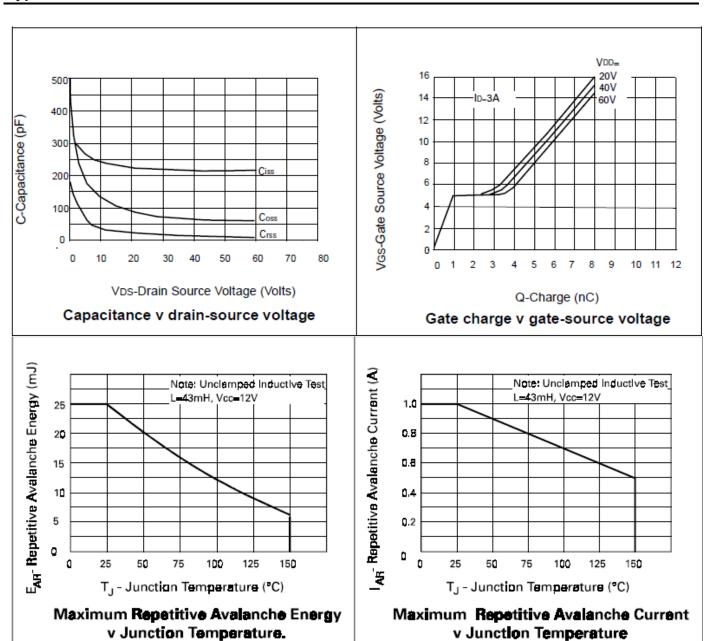


### **Typical Characteristics**





## **Typical Characteristics**

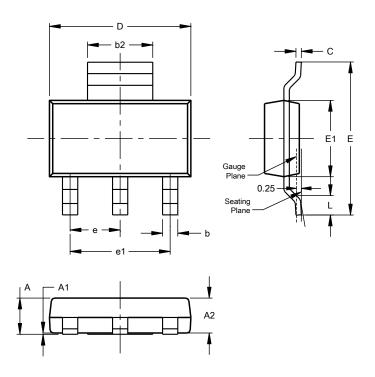




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

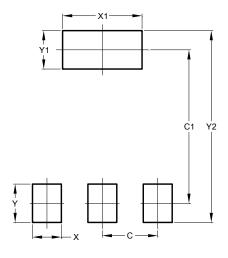


| SOT223 (Type DN)     |      |      |      |  |  |
|----------------------|------|------|------|--|--|
| Dim                  | Min  | Max  | Тур  |  |  |
| Α                    |      | 1.70 |      |  |  |
| A1                   | 0.01 | 0.15 |      |  |  |
| A2                   | 1.50 | 1.68 | 1.60 |  |  |
| b                    | 0.60 | 0.80 | 0.70 |  |  |
| b2                   | 2.90 | 3.10 |      |  |  |
| С                    | 0.20 | 0.32 |      |  |  |
| D                    | 6.30 | 6.70 |      |  |  |
| Е                    | 6.70 | 7.30 |      |  |  |
| E1                   | 3.30 | 3.70 |      |  |  |
| е                    |      |      | 2.30 |  |  |
| e1                   |      |      | 4.60 |  |  |
| L                    | 0.85 |      |      |  |  |
| All Dimensions in mm |      |      |      |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.30          |
| C1         | 6.40          |
| Х          | 1.20          |
| X1         | 3.30          |
| Y          | 1.60          |
| Y1         | 1.60          |
| Y2         | 8 00          |



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